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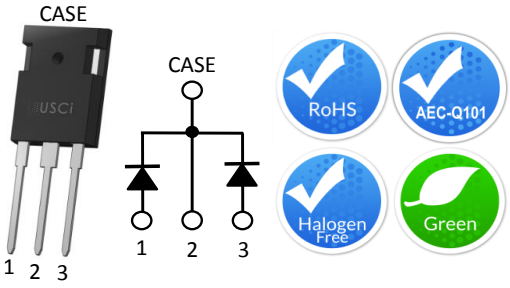
Gen-III | 10A - 1200V SiC Schottky Diode | UJ3D1210KSD

Datasheet

Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D1210KSD	TO-247-3L	UJ3D1210KSD

Features

- 175°C maximum operating junction temperature
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- Excellent thermal performance, Ag sintered
- 100% UIS tested
- AEC-Q101 qualified

Typical Applications

- Power converters
- Industrial motor drives
- Switching-mode power supplies
- Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value (Leg/Device)	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, T_j=25°C	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	T_C = 160.7°C	5/10	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	T_C = 25°C, t_p = 10ms	70/140	A
		T_C = 110°C, t_p =10ms	63/126	
Repetitive forward surge current sine halfwave, D=0.1	I_{FRM}	T_C = 25°C, t_p = 10ms	31.8/63.6	A
		T_C = 110°C, t_p =10ms	18.6/37.2	
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25°C, t_p =10µs	525/1050	A
		T_C = 110°C, t_p =10µs	525/1050	
i^2t value	$\int i^2dt$	T_C = 25°C, t_p =10ms	24.5/98	A^2s
		T_C = 110°C, t_p =10ms	19.5/78	
Power dissipation	P_{Tot}	T_C = 25°C	136/272	W
		T_C = 160.7°C	13/26	
Maximum junction temperature	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	°C

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Electrical Characteristics

T_J = +25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Forward voltage	V_F	I_F = 5A/10A, T_J = 25°C	-	1.4	1.6	V
		I_F = 5A/10A, T_J =150°C	-	1.85	2.3	
		I_F = 5A/10A, T_J =175°C	-	2	2.6	
Reverse current	I_R	V_R=1200V, T_j=25°C	-	40/80	210/420	µA
		V_R=1200V, T_j=175°C	-	400/800		
Total capacitive charge (1)	Q_C	V_R=800V		27/54		nC
Total capacitance	C	V_R=1V, f=1MHz		250/500		pF
		V_R=400V, f=1MHz		24.5/49		
		V_R=800V, f=1MHz		22/44		
Capacitance stored energy	E_C	V_R=800V		8/16		µJ

(1) Q_c is independent on T_j, di_F/dt, and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			0.85/0.425	1.1/0.55	°C/W

Typical Performance (Per Leg)

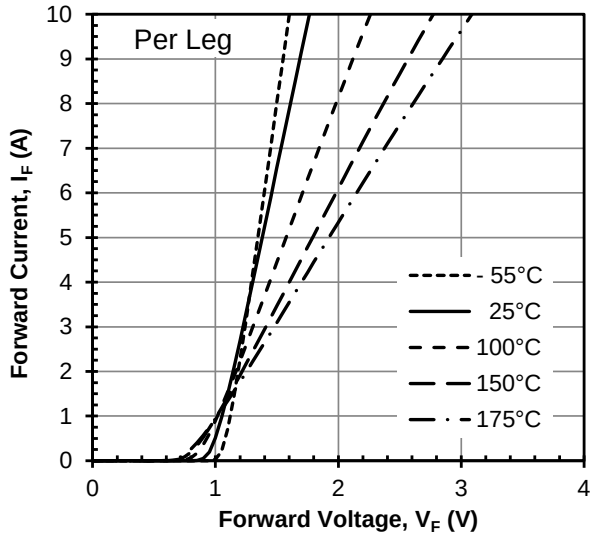

Figure 1 Typical forward characteristics

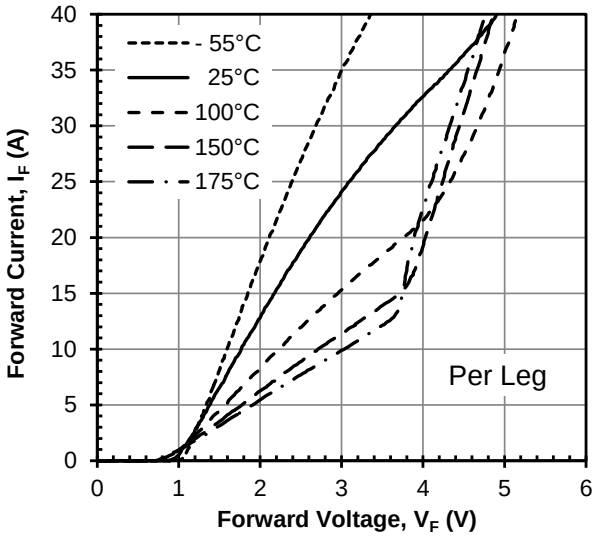

Figure 2 Typical forward characteristics in surge current

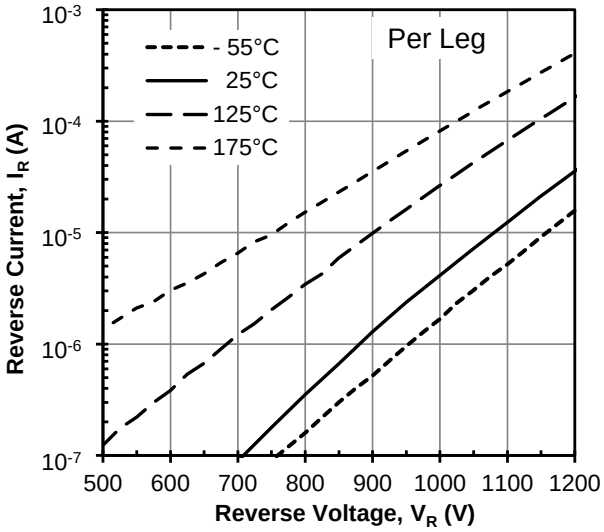

Figure 3 Typical reverse characteristics

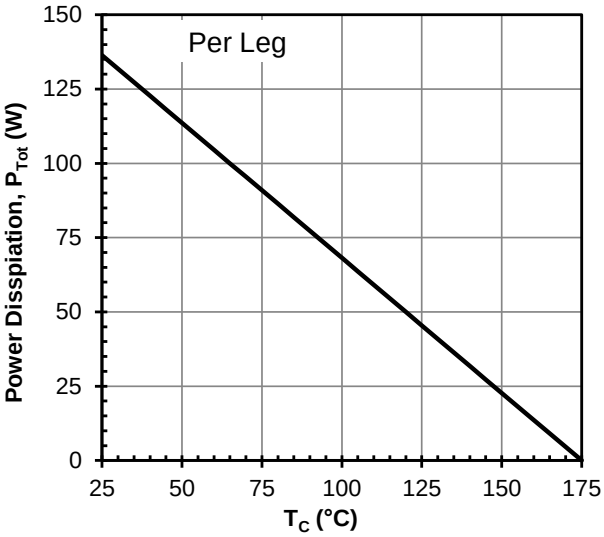

Figure 4 Power dissipation

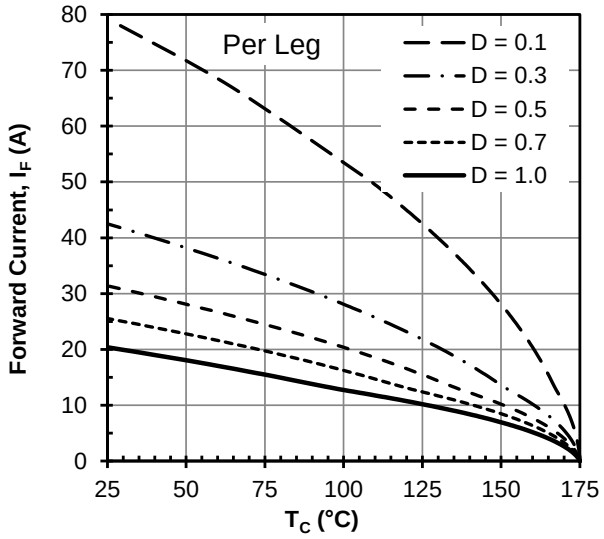

Figure 5 Diode forward current

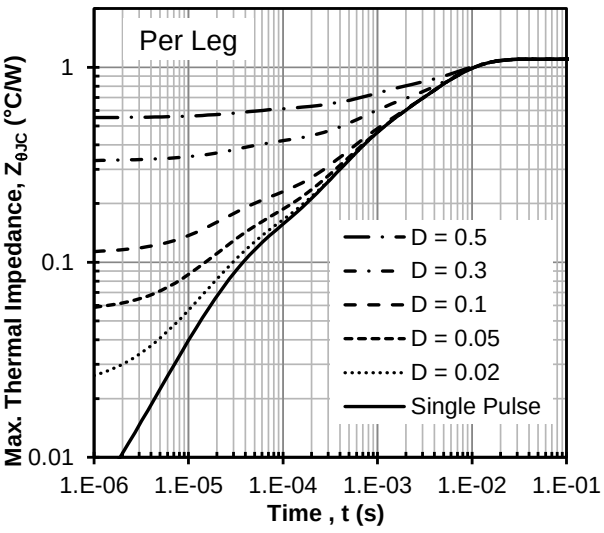

Figure 6 Maximum transient thermal impedance

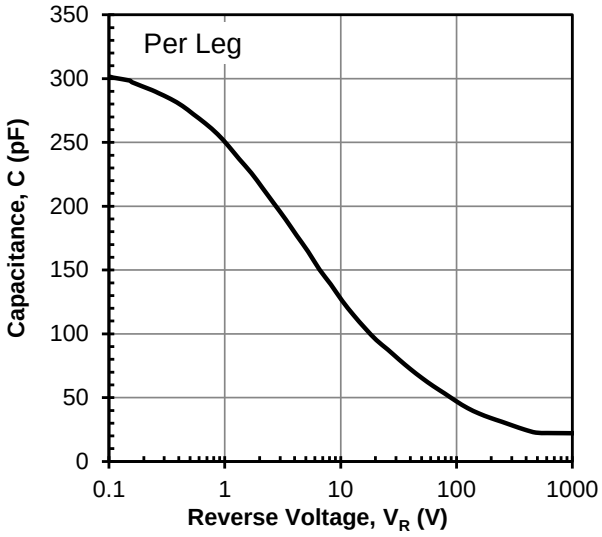

Figure 7 Capacitance vs. reverse voltage at 1MHz

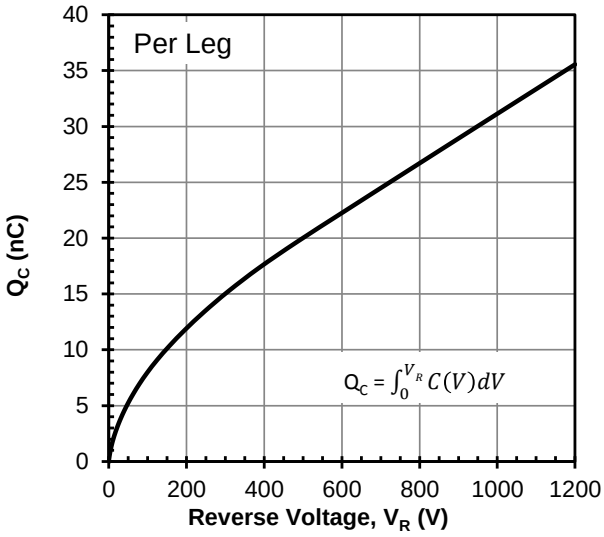

Figure 8 Typical capacitive charge vs. reverse voltage

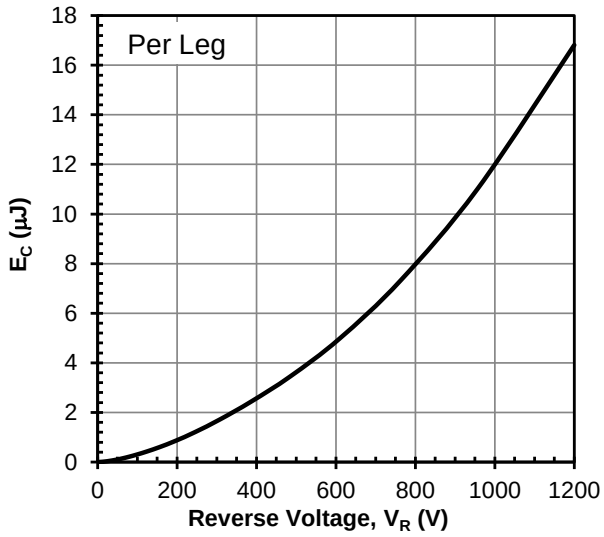

Figure 9 Typical capacitance stored energy vs. reverse voltage

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Angst+Pfister
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We are here for you. Addresses and Contacts.

Headquarter Switzerland:

Angst+Pfister Sensors and Power AG
Thurgauerstrasse 66
CH-8050 Zurich
Phone +41 44 877 35 00
sensorsandpower@angst-pfister.com

Office Germany:

Angst+Pfister Sensors and Power Deutschland GmbH
Edisonstraße 16
D-85716 Unterschleißheim
Phone +49 89 374 288 87 00
sensorsandpower.de@angst-pfister.com

Scan here and get an overview of personal contacts!

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